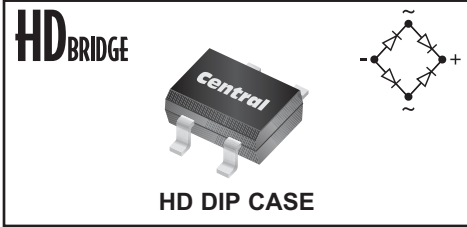


CBRHDSH1-200
SURFACE MOUNT
HIGH DENSITY
1 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centrasemi.com



DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRHDSH1-200 is a full wave bridge rectifier in a durable surface mount epoxy molded case, designed for high voltage full wave rectification applications. The molding compound used in this device has UL flammability classification 94V-O.

MARKING CODE: CSH120

FEATURES:

- Low forward voltage (0.76V TYP @ 1.0A)
- Low leakage current (0.2μA TYP @ 200V)
- High current rating: 1.0A
- High voltage rating: 200V

APPLICATIONS:

- Input rectification for LED lighting
- Power over ethernet (PoE) peripherals
- General purpose full wave rectification

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
DC Blocking Voltage	V_R	200	V
RMS Reverse Voltage	$V_{R(RMS)}$	140	V
Average Forward Current	I_O	1.0	A
Peak Forward Surge Current	I_{FSM}	20	A
Power Dissipation	P_D	1.2	W
Operating Junction Temperature	T_J	-50 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-50 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	85	$^{\circ}\text{C/W}$

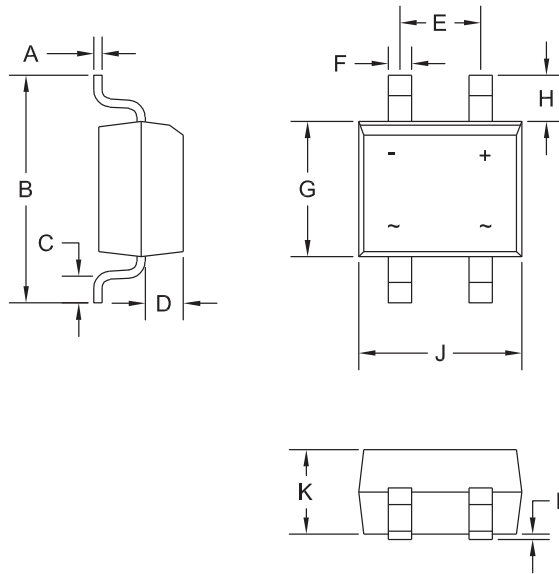
ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=200\text{V}$		0.2	50	μA
I_R	$V_R=200\text{V}, T_A=100^{\circ}\text{C}$			20	mA
BV_R	$I_R=100\mu\text{A}$	200	220		V
V_F	$I_F=1.0\text{A}$		760	900	mV

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HD DIP CASE - MECHANICAL OUTLINE



R2

DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.006	0.014	0.15	0.35
B	-	0.275	-	7.00
C	0.027	0.043	0.70	1.10
D	0.035	0.051	0.90	1.30
E	0.090	0.106	2.30	2.70
F	0.019	0.031	0.50	0.80
G	0.150	0.165	3.80	4.20
H	0.051	0.067	1.30	1.70
J	0.177	0.193	4.50	4.90
K	0.090	0.106	2.30	2.70
L	0.000	0.008	0.00	0.20

HD DIP (REV: R2)

MARKING CODE: CSH120

R1 (5-January 2012)